## **Silicon Power Transistors**

The MJ15023 and MJ15025 are PowerBase power transistors designed for high power audio, disk head positioners and other linear applications.

- High Safe Operating Area (100% Tested) 2 A @ 80 V
- High DC Current Gain —
   hFE = 15 (Min) @ IC = 8 Adc

# MJ15023 MJ15025\*

\*Motorola Preferred Device

16 AMPERE SILICON POWER TRANSISTORS 200 AND 250 VOLTS 250 WATTS



CASE 1-07 TO-204AA (TO-3)

#### **MAXIMUM RATINGS**

Rating	Symbol	MJ15023	MJ15025	Unit
Collector–Emitter Voltage	VCEO	200	250	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	350	400	Vdc
Emitter-Base Voltage	VEBO	5		Vdc
Collector-Emitter Voltage	VCEX	400		Vdc
Collector Current — Continuous Peak (1)	lc	16 30		Adc
Base Current — Continuous	IB	5		Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	250 1.43		Watts W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>Stg</sub>	-65 to +200		°C

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	0.70	°C/W

(1) Pulse Test: Pulse Width = 5 ms, Duty Cycle ≤ 10%.

Preferred devices are Motorola recommended choices for future use and best overall value.



#### MJ15023 MJ15025

### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS		•			•
Collector–Emitter Sustaining Voltage (1) (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 0)	MJ15023 MJ15025	VCEO(sus)	200 250		
Collector Cutoff Current (VCE = 200 Vdc, VBE(off) = 1.5 Vdc) (VCE = 250 Vdc, VBE(off) = 1.5 Vdc)	MJ15023 MJ15025	ICEX		250 250	μAdc
Collector Cutoff Current ( $V_{CE} = 150 \text{ Vdc}$ , $I_{B} = 0$ ) ( $V_{CE} = 200 \text{ Vdc}$ , $I_{B} = 0$ )	MJ15023 MJ15025	ICEO		500 500	μAdc
Emitter Cutoff Current (V <sub>CE</sub> = 5 Vdc, I <sub>B</sub> = 0)	Both	I <sub>EBO</sub>	_	500	μAdc
SECOND BREAKDOWN					
Second Breakdown Collector Current with Base Forward Biased (V <sub>CE</sub> = 50 Vdc, t = 0.5 s (non-repetitive)) (V <sub>CE</sub> = 80 Vdc, t = 0.5 s (non-repetitive))		I <sub>S/b</sub>	5 2	_	Adc
ON CHARACTERISTICS					
DC Current Gain (I <sub>C</sub> = 8 Adc, V <sub>CE</sub> = 4 Vdc) (I <sub>C</sub> = 16 Adc, V <sub>CE</sub> = 4 Vdc)		hFE	15 5	60 —	_
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 8 Adc, I <sub>B</sub> = 0.8 Adc) (I <sub>C</sub> = 16 Adc, I <sub>B</sub> = 3.2 Adc)		VCE(sat)	_	1.4 4.0	Vdc
Base–Emitter On Voltage (I <sub>C</sub> = 8 Adc, V <sub>CE</sub> = 4 Vdc)		VBE(on)	_	2.2	Vdc
DYNAMIC CHARACTERISTICS					-
Current–Gain — Bandwidth Product (I <sub>C</sub> = 1 Adc, V <sub>CE</sub> = 10 Vdc, f <sub>test</sub> = 1 MHz)		fΤ	4	_	MHz
Output Capacitance $(V_{CB} = 10 \text{ Vdc}, I_E = 0, f_{test} = 1 \text{ MHz})$		C <sub>ob</sub>	_	600	pF

<sup>(1)</sup> Pulse Test: Pulse Width = 300  $\mu$ s, Duty Cycle  $\leq$  2%.

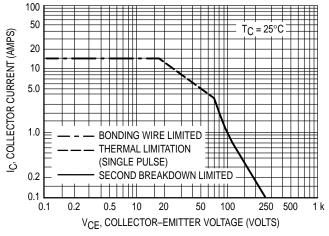


Figure 1. Active-Region Safe Operating Area

There are two limitations on the powerhandling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I<sub>C</sub> – V<sub>CE</sub> limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 1 is based on  $T_{J(pk)} = 200\,^{\circ}\text{C}$ ;  $T_{C}$  is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

### **TYPICAL CHARACTERISTICS**

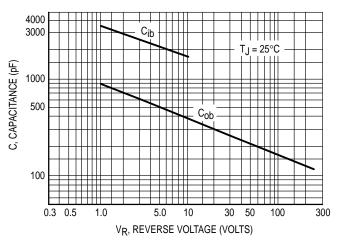


Figure 2. Capacitances

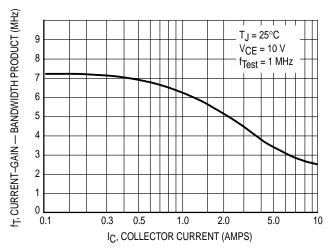


Figure 3. Current-Gain — Bandwidth Product

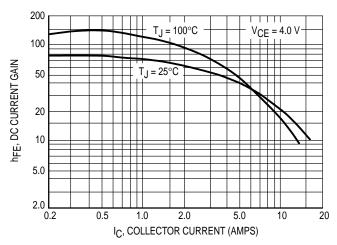


Figure 4. DC Current Gain

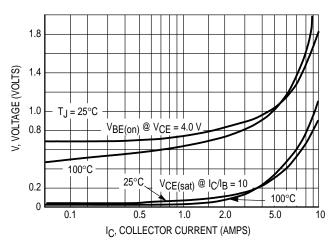
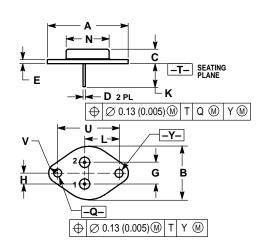


Figure 5. "On" Voltages

#### PACKAGE DIMENSIONS



- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
- ALL RULES AND NOTES ASSOCIATED WITH
   REFERENCED TO-204AA OUTLINE SHALL APPLY.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	1.550 REF		39.37 REF		
В		1.050		26.67	
С	0.250	0.335	6.35	8.51	
D	0.038	0.043	0.97	1.09	
E	0.055	0.070	1.40	1.77	
G	0.430 BSC		10.92 BSC		
Н	0.215 BSC		5.46 BSC		
K	0.440	0.480	11.18	12.19	
L	0.665 BSC		16.89 BSC		
N		0.830		21.08	
Q	0.151	0.165	3.84	4.19	
U	1.187	BSC	30.15 BSC		
٧	0.131	0.188	3.33	4.77	

STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR

**CASE 1-07** TO-204AA (TO-3) **ISSUE Z** 

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